

### **isc Silicon NPN Power Transistor**

# 2SC4689

### DESCRIPTION

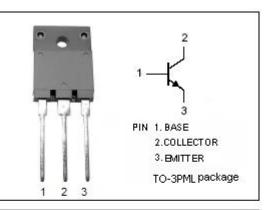
- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 120V(Min)
- Collector-Emitter Saturation Voltage-
- : V<sub>CE(sat)</sub>= 2.0V(Max)@ I<sub>C</sub>= 6A
- Complement to Type 2SA1804
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

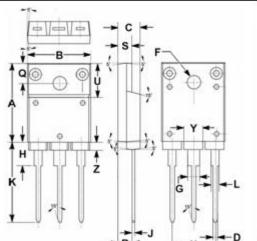
#### **APPLICATIONS**

- Power amplifier applications
- Recommend for 55W high fidelity audio frequency
  amplifier output stage applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	CBO Collector-Base Voltage		V
V <sub>CEO</sub>	Collector-Emitter Voltage	120	V
V <sub>EBO</sub> Emitter-Base voltage		5	V
lc	I <sub>C</sub> Collector Current-Continuous		А
Ісм	Collector Current-Peak	16	А
IB	I <sub>B</sub> Base Current-Continuous		А
Pc	$P_c$ Collector Power Dissipation @ T <sub>c</sub> =25°C		W
TJ	Junction Temperature	150	°C
Tstg	Storage Temperature Range	-55~150	°C





	m	m
DIM	MIN	MAX
Α	19.90	20.10
В	15.90	16.10
С	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
Η	5.90	6.10
J	0.595	0.605
к	22.30	22.50
LN	1.90	2.10
	10.80	11.00
0	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	120			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 0.6A			2.0	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V			1.5	V
I <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			5.0	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5.0	μA
hfe-1	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	55		160	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V	35			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		30		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		190		pF

### • h<sub>FE-1</sub> Classifications

R	о
55-110	80-160



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